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#### Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

**Embedded - System On Chip (SoC)** refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

#### What are **Embedded - System On Chip (SoC)**?

**System On Chip (SoC)** integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions. SoCs combine a central

#### Details

Product Status	Active
Architecture	MCU, FPGA
Core Processor	ARM® Cortex®-M3
Flash Size	512KB
RAM Size	64KB
Peripherals	DMA, POR, WDT
Connectivity	EBI/EMI, Ethernet, I²C, SPI, UART/USART
Speed	80MHz
Primary Attributes	ProASIC®3 FPGA, 500K Gates, 11520 D-Flip-Flops
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a2f500m3g-fgg484

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

## Package I/Os: MSS + FPGA I/Os

Device		A2F060 <sup>1</sup>			A2F	<b>200</b> <sup>2</sup>		A2F500 <sup>2</sup>					A2F500 <sup>2</sup>			
Package	TQ144	CS288	FG256	PQ208	CS288	FG256	FG484	PQ208	CS288	FG256	FG484					
Direct Analog Inputs	11	11	11	8	8	8	8	8	8	8	12					
Shared Analog Inputs	4	4	4	16	16	16	16	16	16	16	20					
Total Analog Inputs	15	15	15	24	24	24	24	24	24	24	32					
Analog Outputs	1	1	1	1	2	2	2	1	2	2	3					
MSS I/Os <sup>3,4</sup>	21 <sup>5</sup>	28 <sup>5</sup>	26 <sup>5</sup>	22	31	25	41	22	31	25	41					
FPGA I/Os	33 <sup>6</sup>	68	66	66	78	66	94	66 <sup>6</sup>	78	66	128					
Total I/Os	70	112	108	113	135	117	161	113	135	117	204					

#### Notes:

1. There are no LVTTL capable direct inputs available on A2F060 devices.

2. These pins are shared between direct analog inputs to the ADCs and voltage/current/temperature monitors.

3. 16 MSS I/Os are multiplexed and can be used as FPGA I/Os, if not needed for MSS. These I/Os support Schmitt triggers and support only LVTTL and LVCMOS (1.5 / 1.8 / 2.5, 3.3 V) standards.

4. 9 MSS I/Os are primarily for 10/100 Ethernet MAC and are also multiplexed and can be used as FPGA I/Os if Ethernet MAC is not used in a design. These I/Os support Schmitt triggers and support only LVTTL and LVCMOS (1.5 / 1.8 / 2.5, 3.3 V standards.

5. 10/100 Ethernet MAC is not available on A2F060.

6. EMC is not available on the A2F500 PQ208 and A2F060 TQ144 package.

#### Table 1 • SmartFusion cSoC Package Sizes Dimensions

Package	TQ144	PQ208	CS288	FG256	FG484
Length × Width (mm\mm)	20 × 20	28 × 28	11 × 11	17 × 17	23 × 23
Nominal Area (mm <sup>2</sup> )	400	784	121	289	529
Pitch (mm)	0.5	0.5	0.5	1.0	1.0
Height (mm)	1.40	3.40	1.05	1.60	2.23

## SmartFusion cSoC Device Status

Device	Status
A2F060	Preliminary: CS288, FG256, TQ144
A2F200	Production: CS288, FG256, FG484, PQ208
A2F500	Production: CS288, FG256, FG484, PQ208



SmartFusion Family Overview

## ProASIC3 FPGA Fabric

The SmartFusion cSoC family, based on the proven, low power, firm-error immune ProASIC<sup>®</sup>3 flash FPGA architecture, benefits from the advantages only flash-based devices offer:

#### Reduced Cost of Ownership

Advantages to the designer extend beyond low unit cost, high performance, and ease of use. Flashbased SmartFusion cSoCs are Instant On and do not need to be loaded from an external boot PROM at each power-up. On-board security mechanisms prevent access to the programming information and enable secure remote updates of the FPGA logic. Designers can perform secure remote in-system programming (ISP) to support future design iterations and critical field upgrades, with confidence that valuable IP cannot be compromised or copied. Secure ISP can be performed using the industry standard AES algorithm with MAC data authentication on the device.

#### Low Power

Flash-based SmartFusion cSoCs exhibit power characteristics similar to those of an ASIC, making them an ideal choice for power-sensitive applications. With SmartFusion cSoCs, there is no power-on current and no high current transition, both of which are common with SRAM-based FPGAs.

SmartFusion cSoCs also have low dynamic power consumption and support very low power timekeeping mode, offering further power savings.

#### Security

As the nonvolatile, flash-based SmartFusion cSoC family requires no boot PROM, there is no vulnerable external bitstream. SmartFusion cSoCs incorporate FlashLock<sup>®</sup>, which provides a unique combination of reprogrammability and design security without external overhead, advantages that only a device with nonvolatile flash programming can offer.

SmartFusion cSoCs utilize a 128-bit flash-based key lock and a separate AES key to provide security for programmed IP and configuration data. The FlashROM data in Fusion devices can also be encrypted prior to loading. Additionally, the flash memory blocks can be programmed during runtime using the AES-128 block cipher encryption standard (FIPS Publication 192).

SmartFusion cSoCs with AES-based security are designed to provide protection for remote field updates over public networks, such as the Internet, and help to ensure that valuable IP remains out of the hands of system overbuilders, system cloners, and IP thieves. As an additional security measure, the FPGA configuration data of a programmed Fusion device cannot be read back, although secure design verification is possible. During design, the user controls and defines both internal and external access to the flash memory blocks.

Security, built into the FPGA fabric, is an inherent component of the SmartFusion cSoC family. The flash cells are located beneath seven metal layers, and many device design and layout techniques have been used to make invasive attacks extremely difficult. SmartFusion cSoCs, with FlashLock and AES security, are unique in being highly resistant to both invasive and noninvasive attacks. Your valuable IP is protected with industry standard security measures, making remote ISP feasible. A SmartFusion cSoC provides the highest security available for programmable logic designs.

#### Single Chip

Flash-based FPGAs store their configuration information in on-chip flash cells. Once programmed, the configuration data is an inherent part of the FPGA structure, and no external configuration data needs to be loaded at system power-up (unlike SRAM-based FPGAs). Therefore, flash-based SmartFusion cSoCs do not require system configuration components such as electrically erasable programmable read-only memories (EEPROMs) or microcontrollers to load device configuration data during power-up. This reduces bill-of-materials costs and PCB area, and increases system security and reliability.

#### Instant On

Flash-based SmartFusion cSoCs are Instant On. Instant On SmartFusion cSoCs greatly simplify total system design and reduce total system cost by eliminating the need for complex programmable logic devices (CPLDs). SmartFusion Instant On clocking (PLLs) replace off-chip clocking resources. In addition, glitches and brownouts in system power will not corrupt the SmartFusion flash configuration. Unlike SRAM-based FPGAs, the device will not have to be reloaded when system power is restored.

SmartFusion Customizable System-on-Chip (cSoC)

$$P = \frac{T_J - T_A}{\theta_{JA}} = \frac{100^{\circ}C - 70^{\circ}C}{17.00 \text{ W}} = 1.76 \text{ W}$$

EQ 6

The 1.76 W power is less than the required 3.00 W. The design therefore requires a heat sink, or the airflow where the device is mounted should be increased. The design's total junction-to-air thermal resistance requirement can be estimated by EQ 7:

$$\theta_{JA(total)} = \frac{T_J - T_A}{P} = \frac{100^{\circ}C - 70^{\circ}C}{3.00 \text{ W}} = 10.00^{\circ}\text{C/W}$$

EQ 7

Determining the heat sink's thermal performance proceeds as follows:

$$\theta_{JA(TOTAL)} = \theta_{JC} + \theta_{CS} + \theta_{SA}$$

EQ 8

where

$$\theta_{JA} = 0.37^{\circ}C/W$$

 Thermal resistance of the interface material between the case and the heat sink, usually provided by the thermal interface manufacturer

 $\theta_{SA}$  = Thermal resistance of the heat sink in °C/W

 $\theta_{\text{SA}}$ 

$$\theta_{SA} = \theta_{JA(TOTAL)} - \theta_{JC} - \theta_{CS}$$

$$EQ 9$$

$$= 13.33^{\circ}C/W - 8.28^{\circ}C/W - 0.37^{\circ}C/W = 5.01^{\circ}C/W$$

A heat sink with a thermal resistance of 5.01°C/W or better should be used. Thermal resistance of heat sinks is a function of airflow. The heat sink performance can be significantly improved with increased airflow.

Carefully estimating thermal resistance is important in the long-term reliability of an FPGA. Design engineers should always correlate the power consumption of the device with the maximum allowable power dissipation of the package selected for that device.

Note: The junction-to-air and junction-to-board thermal resistances are based on JEDEC standard (JESD-51) and assumptions made in building the model. It may not be realized in actual application and therefore should be used with a degree of caution. Junction-to-case thermal resistance assumes that all power is dissipated through the case.

#### **Temperature and Voltage Derating Factors**

Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays<br/>(normalized to T<sub>J</sub> = 85°C, worst-case VCC = 1.425 V)

Array	Junction Temperature (°C)										
Voltage VCC (V)	–40°C	0°C	25°C	70°C	85°C	100°C					
1.425	0.86	0.91	0.93	0.98	1.00	1.02					
1.500	0.81	0.86	0.88	0.93	0.95	0.96					
1.575	0.78	0.83	0.85	0.90	0.91	0.93					

## **Overview of I/O Performance**

## Summary of I/O DC Input and Output Levels – Default I/O Software Settings

#### Table 2-19 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial Conditions—Software Default Settings Applicable to FPGA I/O Banks

			VIL		VIH		VOL	VOH	I <sub>OL</sub> <sup>1</sup>	I <sub>OH</sub> 1	
I/O Standard	Drive Strgth.			Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	High	-0.3	0.8	2	3.6	0.4	2.4	12	12	
2.5 V LVCMOS	12 mA	High	-0.3	0.7	1.7	3.6	0.7	1.7	12	12	
1.8 V LVCMOS	12 mA	High	-0.3	0.35 * VCCxxxxIOBx	0.65* VCCxxxxIOBx	3.6	0.45	VCCxxxxIOBx - 0.45	12	12	
1.5 V LVCMOS	12 mA	High	-0.3	0.35 * VCCxxxxIOBx	0.65* VCCxxxxIOBx	3.6	0.25 * VCCxxxxIOBx	0.75* VCCxxxxIOBx	12	12	
3.3 V PCI		-			Per PCI spec	cificatio	ons	-	-	-	
3.3 V PCI-X		Per PCI-X specifications									

Notes:

1. Currents are measured at 85°C junction temperature.

2. Output slew rate can be extracted by the IBIS Models.

# Table 2-20 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial Conditions—Software Default Settings Applicable to MSS I/O Banks

			VIL		VIH		VOL	VOH	I <sub>OL</sub> <sup>1</sup>	I <sub>OH</sub> 1
I/O Standard	Drive Strgth.	Slew Rate		Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	High	-0.3	0.8	2	3.6	0.4	2.4	8	8
2.5 V LVCMOS	8 mA	High	-0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	High	-0.3	0.35* VCCxxxxIOBx	0.65* VCCxxxxIOBx	3.6	0.45	VCCxxxxIOBx - 0.45	4	4
1.5 V LVCMOS	2 mA	High	-0.3	0.35* VCCxxxxIOBx	0.65* VCCxxxxIOBx	3.6	0.25* VCCxxxxIOBx	0.75* VCCxxxxIOBx	2	2

Notes:

1. Currents are measured at 85°C junction temperature.

2. Output slew rate can be extracted by the IBIS Models.



SmartFusion DC and Switching Characteristics

## Single-Ended I/O Characteristics

#### 3.3 V LVTTL / 3.3 V LVCMOS

Low-Voltage Transistor–Transistor Logic (LVTTL) is a general-purpose standard (EIA/JESD) for 3.3 V applications. It uses an LVTTL input buffer and push-pull output buffer.

#### Table 2-35 • Minimum and Maximum DC Input and Output Levels Applicable to FPGA I/O Banks

3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIH		VOL	VOH	I <sub>OL</sub>	I <sub>OH</sub>	I <sub>OSL</sub>	I <sub>OSH</sub>	I <sub>IL</sub>	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>1</sup>	Max. mA <sup>1</sup>	μA²	μA²
2 mA	-0.3	0.8	2	3.6	0.4	2.4	2	2	27	25	15	15
4 mA	-0.3	0.8	2	3.6	0.4	2.4	4	4	27	25	15	15
6 mA	-0.3	0.8	2	3.6	0.4	2.4	6	6	54	51	15	15
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	15	15
12 mA	-0.3	0.8	2	3.6	0.4	2.4	12	12	109	103	15	15
16 mA	-0.3	0.8	2	3.6	0.4	2.4	16	16	127	132	15	15
24 mA	-0.3	0.8	2	3.6	0.4	2.4	24	24	181	268	10	10

Notes:

1. Currents are measured at 100°C junction temperature and maximum voltage.

2. Currents are measured at 85°C junction temperature.

3. Software default selection highlighted in gray.

#### Table 2-36 • Minimum and Maximum DC Input and Output Levels Applicable to MSS I/O Banks

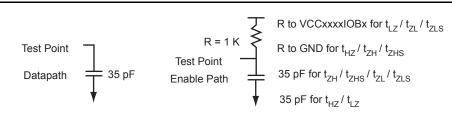
3.3 V LVTTL / 3.3 V LVCMOS	VIL		VIL VIH VOL		VOH	I <sub>OL</sub>	I <sub>OH</sub>	I <sub>OSL</sub>	I <sub>OSH</sub>	I <sub>IL</sub>	I <sub>IH</sub>	
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA <sup>1</sup>	Max. mA <sup>1</sup>	μA²	μA²
8 mA	-0.3	0.8	2	3.6	0.4	2.4	8	8	54	51	15	15

Notes:

1. Currents are measured at 100°C junction temperature and maximum voltage.

2. Currents are measured at 85°C junction temperature.

3. Software default selection highlighted in gray.



#### Figure 2-6 • AC Loading

#### Table 2-37 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V <sub>REF</sub> (typ.) (V)	C <sub>LOAD</sub> (pF)
0	3.3	1.4	-	35

Note: \*Measuring point =  $V_{trip}$ . See Table 2-22 on page 2-24 for a complete table of trip points.

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SmartFusion DC and Switching Characteristics

#### **Timing Characteristics**

# Table 2-56 • 1.5 V LVCMOS High Slew Worst Commercial-Case Conditions: T<sub>J</sub> = 85°C, Worst-Case VCC = 1.425 V, Worst-Case VCCxxxxIOBx = 1.425 V Applies bla to EDCA VO Basks VC Applies to EMC VO Bins

Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>zH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	t <sub>zLS</sub>	t <sub>zHS</sub>	Units
2 m	Std.	0.60	7.79	0.04	1.34	0.39	6.43	7.79	3.19	2.59	8.49	9.85	ns
	–1	0.50	6.49	0.03	1.12	0.32	5.36	6.49	2.66	2.16	7.08	8.21	ns
4 mA	Std.	0.60	4.95	0.04	1.34	0.39	4.61	4.96	3.53	3.19	6.67	7.02	ns
	–1	0.50	4.13	0.03	1.12	0.32	3.85	4.13	2.94	2.66	5.56	5.85	ns
6 mA	Std.	0.60	4.36	0.04	1.34	0.39	4.34	4.36	3.60	3.34	6.40	6.42	ns
	–1	0.50	3.64	0.03	1.12	0.32	3.62	3.64	3.00	2.78	5.33	5.35	ns
8 mA	Std.	0.60	3.89	0.04	1.34	0.39	3.96	3.34	3.72	3.92	6.02	5.40	ns
	-1	0.50	3.24	0.03	1.12	0.32	3.30	2.79	3.10	3.27	5.02	4.50	ns
12 mA	Std.	0.60	3.89	0.04	1.34	0.39	3.96	3.34	3.72	3.92	6.02	5.40	ns
	-1	0.50	3.24	0.03	1.12	0.32	3.30	2.79	3.10	3.27	5.02	4.50	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

#### Table 2-57 • 1.5 V LVCMOS Low Slew

Worst Commercial-Case Conditions:  $T_J = 85^{\circ}C$ , Worst-Case VCC = 1.425 V, Worst-Case VCCxxxxIOBx = 1.4 V Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>EOUT</sub>	t <sub>ZL</sub>	t <sub>zH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	t <sub>zLS</sub>	t <sub>zHS</sub>	Units
2 mA	Std.	0.60	11.96	0.04	1.34	0.39	12.18	11.70	3.20	2.47	14.24	13.76	ns
	-1	0.50	9.96	0.03	1.12	0.32	10.15	9.75	2.67	2.06	11.86	11.46	ns
4 mA	Std.	0.60	9.51	0.04	1.34	0.39	9.68	8.76	3.54	3.07	11.74	10.82	ns
	-1	0.50	7.92	0.03	1.12	0.32	8.07	7.30	2.95	2.56	9.79	9.02	ns
6 mA	Std.	0.60	8.86	0.04	1.34	0.39	9.03	8.17	3.61	3.22	11.08	10.23	ns
	-1	0.50	7.39	0.03	1.12	0.32	7.52	6.81	3.01	2.68	9.24	8.52	ns
8 mA	Std.	0.60	8.44	0.04	1.34	0.39	8.60	8.18	3.73	3.78	10.66	10.24	ns
	-1	0.50	7.04	0.03	1.12	0.32	7.17	6.82	3.11	3.15	8.88	8.53	ns
12 mA	Std.	0.60	8.44	0.04	1.34	0.39	8.60	8.18	3.73	3.78	10.66	10.24	ns
	-1	0.50	7.04	0.03	1.12	0.32	7.17	6.82	3.11	3.15	8.88	8.53	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

#### Table 2-58 • 1.5 V LVCMOS High Slew

Worst Commercial-Case Conditions: T<sub>J</sub> = 85°C, Worst-Case VCC = 1.425 V, Worst-Case VCCxxxxIOBx = 3.0 V Applicable to MSS I/O Banks

Drive Strength	Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	t <sub>PYS</sub>	t <sub>EOUT</sub>	t <sub>zL</sub>	t <sub>zH</sub>	t <sub>LZ</sub>	t <sub>HZ</sub>	Units
2 mA	Std.	0.22	3.24	0.09	1.28	1.86	0.22	3.30	3.20	2.24	2.21	ns
	-1	0.18	2.70	0.07	1.07	1.55	0.18	2.75	2.67	1.87	1.85	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

DC Parameter	Description	Min.	Тур.	Max.	Units
VCCFPGAIOBx	Supply voltage	2.375	2.5	2.625	V
VOL	Output low voltage	0.9	1.075	1.25	V
VOH	Output high voltage	1.25	1.425	1.6	V
I <sub>OL</sub> <sup>1</sup>	Output lower current	0.65	0.91	1.16	mA
I <sub>OH</sub> <sup>1</sup>	Output high current	0.65	0.91	1.16	mA
VI	Input voltage	0		2.925	V
I <sub>IH</sub> <sup>2</sup>	Input high leakage current			15	μΑ
I <sub>IL</sub> <sup>2</sup>	Input low leakage current			15	μA
V <sub>ODIFF</sub>	Differential output voltage	250	350	450	mV
V <sub>OCM</sub>	Output common mode voltage	1.125	1.25	1.375	V
V <sub>ICM</sub>	Input common mode voltage	0.05	1.25	2.35	V
V <sub>IDIFF</sub>	Input differential voltage	100	350		mV

Notes:

1.  $I_{OL}/I_{OH}$  defined by  $V_{ODIFF}$  (resistor network).

2. Currents are measured at 85°C junction temperature.

#### Table 2-64 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	V <sub>REF</sub> (typ.) (V)
1.075	1.325	Cross point	-

\* Measuring point =  $V_{trip.}$  See Table 2-22 on page 2-24 for a complete table of trip points.

#### **Timing Characteristics**

#### Table 2-65 • LVDS

#### Worst Commercial-Case Conditions: T<sub>J</sub> = 85°C, Worst-Case VCC = 1.425 V, Worst-Case VCCFPGAIOBx = 2.3 V Applicable to FPGA I/O Banks, I/O Assigned to EMC I/O Pins

Speed Grade	t <sub>DOUT</sub>	t <sub>DP</sub>	t <sub>DIN</sub>	t <sub>PY</sub>	Units
Std.	0.60	1.83	0.04	1.87	ns
-1	0.50	1.53	0.03	1.55	ns

Notes:

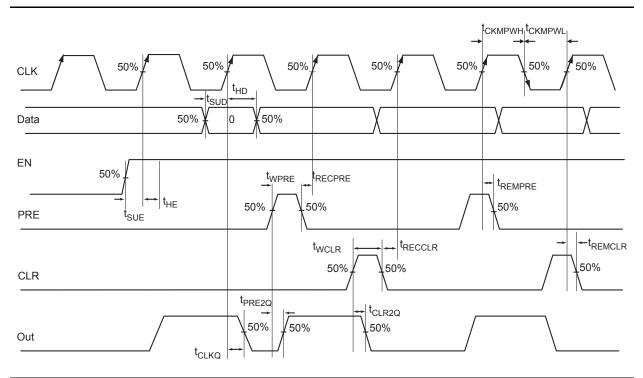
1. For the derating values at specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.

2. The above mentioned timing parameters correspond to 24mA drive strength.

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t <sub>oclkq</sub>	Clock-to-Q of the Output Data Register	HH, DOUT
tosud	Data Setup Time for the Output Data Register	FF, HH
t <sub>ОНD</sub>	Data Hold Time for the Output Data Register	FF, HH
tosue	Enable Setup Time for the Output Data Register	GG, HH
t <sub>OHE</sub>	Enable Hold Time for the Output Data Register	GG, HH
t <sub>OCLR2Q</sub>	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
t <sub>OREMCLR</sub>	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
t <sub>ORECCLR</sub>	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t <sub>oeclkq</sub>	Clock-to-Q of the Output Enable Register	HH, EOUT
tOESUD	Data Setup Time for the Output Enable Register	JJ, HH
t <sub>OEHD</sub>	Data Hold Time for the Output Enable Register	JJ, HH
tOESUE	Enable Setup Time for the Output Enable Register	KK, HH
t <sub>OEHE</sub>	Enable Hold Time for the Output Enable Register	KK, HH
t <sub>OECLR2Q</sub>	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
t <sub>OEREMCLR</sub>	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
t <sub>OERECCLR</sub>	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t <sub>ICLKQ</sub>	Clock-to-Q of the Input Data Register	AA, EE
t <sub>ISUD</sub>	Data Setup Time for the Input Data Register	CC, AA
t <sub>IHD</sub>	Data Hold Time for the Input Data Register	CC, AA
t <sub>ISUE</sub>	Enable Setup Time for the Input Data Register	BB, AA
t <sub>IHE</sub>	Enable Hold Time for the Input Data Register	BB, AA
t <sub>ICLR2Q</sub>	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
t <sub>IREMCLR</sub>	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
t <sub>IRECCLR</sub>	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

#### Table 2-70 • Parameter Definition and Measuring Nodes

\* See Figure 2-15 on page 2-46 for more information.





#### **Timing Characteristics**

#### Table 2-79 • Register Delays

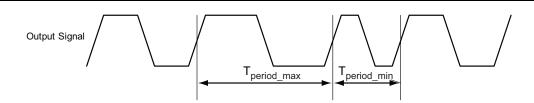
#### Worst Commercial-Case Conditions: T<sub>J</sub> = 85°C, Worst-Case VCC = 1.425 V

Parameter	Description	-1	Std.	Units
t <sub>CLKQ</sub>	Clock-to-Q of the Core Register	0.56	0.67	ns
t <sub>SUD</sub>	Data Setup Time for the Core Register	0.44	0.52	ns
t <sub>HD</sub>	Data Hold Time for the Core Register	0.00	0.00	ns
t <sub>SUE</sub>	Enable Setup Time for the Core Register	0.46	0.55	ns
t <sub>HE</sub>	Enable Hold Time for the Core Register	0.00	0.00	ns
t <sub>CLR2Q</sub>	Asynchronous Clear-to-Q of the Core Register	0.41	0.49	ns
t <sub>PRE2Q</sub>	Asynchronous Preset-to-Q of the Core Register	0.41	0.49	ns
t <sub>REMCLR</sub>	Asynchronous Clear Removal Time for the Core Register	0.00	0.00	ns
t <sub>RECCLR</sub>	Asynchronous Clear Recovery Time for the Core Register	0.23	0.27	ns
t <sub>REMPRE</sub>	Asynchronous Preset Removal Time for the Core Register	0.00	0.00	ns
t <sub>RECPRE</sub>	Asynchronous Preset Recovery Time for the Core Register	0.23	0.27	ns
t <sub>WCLR</sub>	Asynchronous Clear Minimum Pulse Width for the Core Register	0.22	0.22	ns
t <sub>WPRE</sub>	Asynchronous Preset Minimum Pulse Width for the Core Register	0.22	0.22	ns
t <sub>CKMPWH</sub>	Clock Minimum Pulse Width High for the Core Register	0.32	0.32	ns
t <sub>CKMPWL</sub>	Clock Minimum Pulse Width Low for the Core Register	0.36	0.36	ns

*Note:* For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-9 for derating values.



SmartFusion DC and Switching Characteristics



*Note:* Peak-to-peak jitter measurements are defined by  $T_{peak-to-peak} = T_{period_max} - T_{period_min}$ . *Figure 2-28* • Peak-to-Peak Jitter Definition

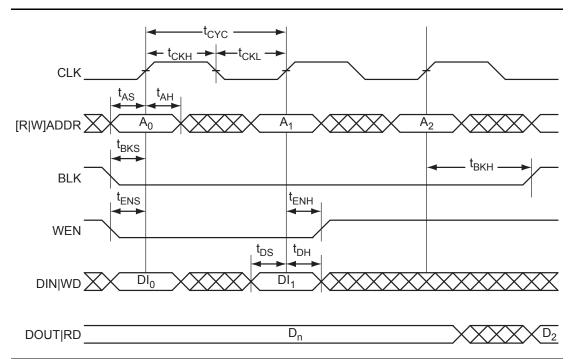


Figure 2-32 • RAM Write, Output Retained. Applicable to both RAM4K9 and RAM512x18.

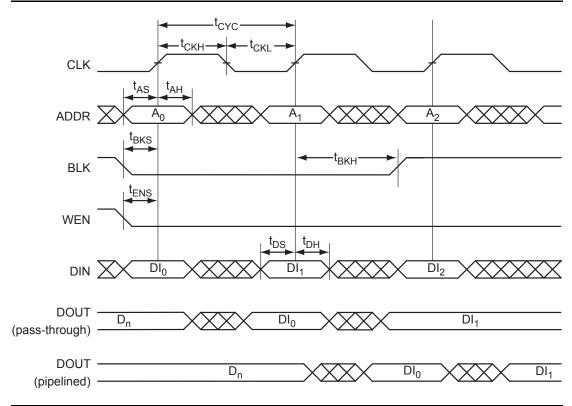


Figure 2-33 • RAM Write, Output as Write Data (WMODE = 1). Applicable to RAM4K9 only.

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SmartFusion DC and Switching Characteristics

## Comparator

Unless otherwise specified, performance is specified at 25°C with nominal power supply voltages.

Specification	Test Conditions		Min.	Тур.	Max.	Units
Input voltage range	Minimum			0		V
	Maximum			2.56		V
Input offset voltage	HYS[1:0] = 00			±1	±3	mV
	(no hysteresis)	no hysteresis)				
Input bias current	Comparator 1,	Comparator 1, 3, 5, 7, 9 (measured at 2.56 V)		40	100	nA
	Comparator 0,	2, 4, 6, 8 (measured at 2.56 V)		150	300	nA
Input resistance			10			MΩ
Power supply rejection ratio	DC (0 – 10 KHz	<u>z</u> )	50	60		dB
Propagation delay	100 mV overdri	ve				
	HYS[1:0] = 00					
	(no hysteresis)			15	18	ns
	100 mV overdrive					
	HYS[1:0] = 10					
	(with hysteresis)			25	30	ns
Hysteresis	HYS[1:0] = 00	Typical (25°C)	0	0	±5	mV
(± refers to rising and falling threshold shifts, respectively)		Across all corners (-40°C to +100°C)	0		±5	mV
theshold shifts, respectively)	HYS[1:0] = 01	Typical (25°C)	±3	± 16	±30	mV
		Across all corners (-40°C to +100°C)	0		±36	mV
	HYS[1:0] = 10	Typical (25°C)	±19	± 31	±48	mV
		Across all corners (-40°C to +100°C)	±12		±54	mV
	HYS[1:0] = 11	Typical (25°C)	±80	± 105	±190	mV
		Across all corners (-40°C to +100°C)	±80		±194	mV
Comparator current	VCC33A = 3.3	V (operational mode); COMP_EN = 1	1	•		L
requirements (per comparator)	VCC33A			150	165	μA
	VCC33AP		1	140	165	μA
	VCC15A			1	3	μA

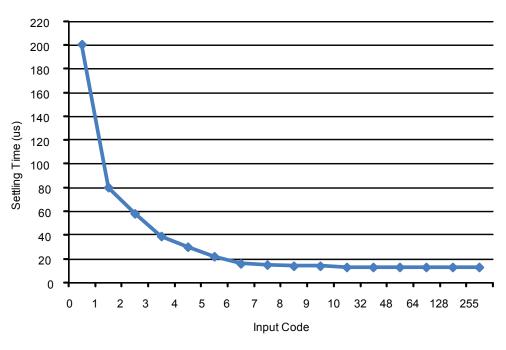


SmartFusion DC and Switching Characteristics

#### Table 2-98 • Analog Sigma-Delta DAC (continued)

Specification	Test Conditions	Min.	Тур.	Max.	Units
Sigma-delta DAC power supply current requirements (not including VAREFx)	Input = 0, EN = 1 (operational mode)				
	VCC33SDDx		30	35	μA
	VCC15A		3	5	μA
	Input = Half scale, EN = 1 (operational mode)				
	VCC33SDDx		160	165	μA
	VCC15A		33	35	μA
	Input = Full scale, EN = 1 (operational mode)				
	VCC33SDDx		280	285	μA
	VCC15A		70	75	μA

Note: \*FS is full-scale error, defined as the difference between the actual value that triggers the transition to full-scale and the ideal analog full-scale transition value. Full-scale error equals offset error plus gain error. Refer to the Analog-to-Digital Converter chapter of the SmartFusion Programmable Analog User's Guide for more information.



#### Sigma Delta DAC Settling Time

Figure 2-44 • Sigma-Delta DAC Setting Time

## **Serial Peripheral Interface (SPI) Characteristics**

This section describes the DC and switching of the SPI interface. Unless otherwise noted, all output characteristics given for a 35 pF load on the pins and all sequential timing characteristics are related to SPI\_x\_CLK. For timing parameter definitions, refer to Figure 2-47 on page 2-90.

Symbol	Description and Condition	A2F060	A2F200	A2F500	Unit
sp1	SPI_x_CLK minimum period			LU	
	SPI_x_CLK = PCLK/2	20	NA	20	ns
	SPI_x_CLK = PCLK/4	40	40	40	ns
	SPI_x_CLK = PCLK/8	80	80	80	ns
	SPI_x_CLK = PCLK/16	0.16	0.16	0.16	μs
	SPI_x_CLK = PCLK/32	0.32	0.32	0.32	μs
	SPI_x_CLK = PCLK/64	0.64	0.64	0.64	μs
	SPI_x_CLK = PCLK/128	1.28	1.28	1.28	μs
	SPI_x_CLK = PCLK/256	2.56	2.56	2.56	μs
sp2	SPI_x_CLK minimum pulse width high				
	SPI_x_CLK = PCLK/2	10	NA	10	ns
	SPI_x_CLK = PCLK/4	20	20	20	ns
	SPI_x_CLK = PCLK/8	40	40	40	ns
	SPI_x_CLK = PCLK/16	0.08	0.08	0.08	μs
	SPI_x_CLK = PCLK/32	0.16	0.16	0.16	μs
	SPI_x_CLK = PCLK/64	0.32	0.32	0.32	μs
	SPI_x_CLK = PCLK/128	0.64	0.64	0.64	μs
	SPI_x_CLK = PCLK/256	1.28	1.28	1.28	us
sp3	SPI_x_CLK minimum pulse width low				
	SPI_x_CLK = PCLK/2	10	NA	10	ns
	SPI_x_CLK = PCLK/4	20	20	20	ns
	SPI_x_CLK = PCLK/8	40	40	40	ns
	SPI_x_CLK = PCLK/16	0.08	0.08	0.08	μs
	SPI_x_CLK = PCLK/32	0.16	0.16	0.16	μs
	SPI_x_CLK = PCLK/64	0.32	0.32	0.32	μs
	SPI_x_CLK = PCLK/128	0.64	0.64	0.64	μs
	SPI_x_CLK = PCLK/256	1.28	1.28	1.28	μs
sp4	SPI_x_CLK, SPI_x_DO, SPI_x_SS rise time (10%-90%) <sup>1</sup>	4.7	4.7	4.7	ns
sp5	SPI_x_CLK, SPI_x_DO, SPI_x_SS fall time (10%-90%) <sup>1</sup>	3.4	3.4	3.4	ns

#### Table 2-100 • SPI Characteristics

Commercial Case Conditions: T<sub>J</sub> = 85°C, VDD = 1.425 V, -1 Speed Grade

Notes:

 These values are provided for a load of 35 pF. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located on the Microsemi SoC Products Group website: http://www.microsemi.com/index.php?option=com\_microsemi&ltemid=489&lang=en&view=salescontact.

2. For allowable pclk configurations, refer to the Serial Peripheral Interface Controller section in the SmartFusion Microcontroller Subsystem User's Guide.

## **5 – Pin Descriptions**

## **Supply Pins**

Name	Туре	Description
GND	Ground	Digital ground to the FPGA fabric, microcontroller subsystem and GPIOs
GND15ADC0	Ground	Quiet analog ground to the 1.5 V circuitry of the first analog-to-digital converter (ADC)
GND15ADC1	Ground	Quiet analog ground to the 1.5 V circuitry of the second ADC
GND15ADC2	Ground	Quite analog ground to the 1.5 V circuitry of the third ADC
GND33ADC0	Ground	Quiet analog ground to the 3.3 V circuitry of the first ADC
GND33ADC1	Ground	Quiet analog ground to the 3.3 V circuitry of the second ADC
GND33ADC2	Ground	Quiet analog ground to the 3.3 V circuitry of the third ADC
GNDA	Ground	Quiet analog ground to the analog front-end
GNDAQ	Ground	Quiet analog ground to the analog I/O of SmartFusion cSoCs
GNDENVM	Ground	Digital ground to the embedded nonvolatile memory (eNVM)
GNDLPXTAL	Ground	Analog ground to the low power 32 KHz crystal oscillator circuitry
GNDMAINXTAL	Ground	Analog ground to the main crystal oscillator circuitry
GNDQ	Ground	Quiet digital ground supply voltage to input buffers of I/O banks. Within the package, the GNDQ plane is decoupled from the simultaneous switching noise originated from the output buffer ground domain. This minimizes the noise transfer within the package and improves input signal integrity. GNDQ needs to always be connected on the board to GND.
GNDRCOSC	Ground	Analog ground to the integrated RC oscillator circuit
GNDSDD0	Ground	Analog ground to the first sigma-delta DAC
GNDSDD1	Ground	Common analog ground to the second and third sigma-delta DACs
GNDTM0	Ground	Analog temperature monitor common ground for signal conditioning blocks SCB 0 and SCB 1 (see information for pins "TM0" and "TM1" in the "Analog Front-End (AFE)" section on page 5-14).
GNDTM1	Ground	Analog temperature monitor common ground for signal conditioning block SCB 2 and SBCB 3 (see information for pins "TM2" and "TM3" in the "Analog Front-End (AFE)" section on page 5-14).
GNDTM2	Ground	Analog temperature monitor common ground for signal conditioning block SCB4
GNDVAREF	Ground	Analog ground reference used by the ADC. This pad should be connected to a quiet analog ground.
VCC	Supply	Digital supply to the FPGA fabric and MSS, nominally 1.5 V. VCC is also required for powering the JTAG state machine, in addition to VJTAG. Even when a SmartFusion cSoC is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the SmartFusion cSoC.

Notes:

1. The following 3.3 V supplies should be connected together while following proper noise filtering practices: VCC33A, VCC33ADCx, VCC33ADCx, VCC33SDDx, VCCMAINXTAL, and VCCLPXTAL.

2. The following 1.5 V supplies should be connected together while following proper noise filtering practices: VCC, VCC15A, and VCC15ADCx.

3. For more details on VCCPLLx capacitor recommendations, refer to the application note AC359, SmartFusion cSoC Board Design Guidelines, the "PLL Power Supply Decoupling Scheme" section.

SmartFusion Customizable System-on-Chip (cSoC)

Pin	FG256				
No.	A2F060 Function	A2F200 Function	A2F500 Function		
A1	GND	GND	GND		
A2	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0		
A3	EMC_AB[0]/IO04NDB0V0	EMC_AB[0]/IO04NDB0V0	EMC_AB[0]/IO06NDB0V0		
A4	EMC_AB[1]/IO04PDB0V0	EMC_AB[1]/IO04PDB0V0	EMC_AB[1]/IO06PDB0V0		
A5	GND	GND	GND		
A6	EMC_AB[3]/IO05PDB0V0	EMC_AB[3]/IO05PDB0V0	EMC_AB[3]/IO09PDB0V0		
A7	EMC_AB[5]/IO06PDB0V0	EMC_AB[5]/IO06PDB0V0	EMC_AB[5]/IO10PDB0V0		
A8	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0		
A9	GND	GND	GND		
A10	EMC_AB[14]/IO11NDB0V0	EMC_AB[14]/IO11NDB0V0	EMC_AB[14]/IO15NDB0V0		
A11	EMC_AB[15]/IO11PDB0V0	EMC_AB[15]/IO11PDB0V0	EMC_AB[15]/IO15PDB0V0		
A12	GND	GND	GND		
A13	EMC_AB[20]/IO14NDB0V0	EMC_AB[20]/IO14NDB0V0	EMC_AB[20]/IO21NDB0V0		
A14	EMC_AB[24]/IO16NDB0V0	EMC_AB[24]/IO16NDB0V0	EMC_AB[24]/IO20NDB0V0		
A15	VCCFPGAIOB0	VCCFPGAIOB0	VCCFPGAIOB0		
A16	GND	GND	GND		
B1	EMC_DB[15]/IO45PDB5V0	EMC_DB[15]/GAA2/IO71PDB5V0	EMC_DB[15]/GAA2/IO88PDB5V0		
B2	GND	GND	GND		
B3	EMC_BYTEN[1]/IO02PDB0V0	EMC_BYTEN[1]/GAC1/IO02PDB0V0	EMC_BYTEN[1]/GAC1/IO07PDB0V0		
B4	EMC_OEN0_N/IO03NDB0V0	EMC_OEN0_N/IO03NDB0V0	EMC_OEN0_N/IO08NDB0V0		
B5	EMC_OEN1_N/IO03PDB0V0	EMC_OEN1_N/IO03PDB0V0	EMC_OEN1_N/IO08PDB0V0		
B6	EMC_AB[2]/IO05NDB0V0	EMC_AB[2]/IO05NDB0V0	EMC_AB[2]/IO09NDB0V0		
B7	EMC_AB[4]/IO06NDB0V0	EMC_AB[4]/IO06NDB0V0	EMC_AB[4]/IO10NDB0V0		
B8	EMC_AB[9]/IO08PDB0V0	EMC_AB[9]/IO08PDB0V0	EMC_AB[9]/IO13PDB0V0		
B9	EMC_AB[12]/IO10NDB0V0	EMC_AB[12]/IO10NDB0V0	EMC_AB[12]/IO14NDB0V0		
B10	EMC_AB[13]/IO10PDB0V0	EMC_AB[13]/IO10PDB0V0	EMC_AB[13]/IO14PDB0V0		
B11	EMC_AB[16]/IO12NDB0V0	EMC_AB[16]/IO12NDB0V0	EMC_AB[16]/IO17NDB0V0		
B12	EMC_AB[18]/IO13NDB0V0	EMC_AB[18]/IO13NDB0V0	EMC_AB[18]/IO18NDB0V0		
B13	EMC_AB[21]/IO14PDB0V0	EMC_AB[21]/IO14PDB0V0	EMC_AB[21]/IO21PDB0V0		
B14	EMC_AB[25]/IO16PDB0V0	EMC_AB[25]/IO16PDB0V0	EMC_AB[25]/IO20PDB0V0		
B15	GND	GND	GND		

#### Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.

SmartFusion Customizable System-on-Chip (cSoC)

Pin No.	FG256				
	A2F060 Function	A2F200 Function	A2F500 Function		
H13	TDO	TDO	TDO		
H14	TDI	TDI	TDI		
H15	JTAGSEL	JTAGSEL	JTAGSEL		
H16	GND	GND	GND		
J1	EMC_DB[4]/IO38NPB5V0	EMC_DB[4]/GEA0/IO61NPB5V0	EMC_DB[4]/GEA0/IO78NPB5V0		
J2	EMC_DB[3]/IO37PDB5V0	EMC_DB[3]/GEC2/IO60PDB5V0	EMC_DB[3]/GEC2/IO77PDB5V0		
J3	EMC_DB[2]/IO37NDB5V0	EMC_DB[2]/IO60NDB5V0	EMC_DB[2]/IO77NDB5V0		
J4	GNDRCOSC	GNDRCOSC	GNDRCOSC		
J5	NC	GNDQ	GNDQ		
J6	GND	GND	GND		
J7	VCC	VCC	VCC		
J8	GND	GND	GND		
J9	VCC	VCC	VCC		
J10	GND	GND	GND		
J11	VCCMSSIOB2	VCCMSSIOB2	VCCMSSIOB2		
J12	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23	I2C_0_SCL/GPIO_23		
J13	I2C_0_SDA/GPIO_22	I2C_0_SDA/GPIO_22	I2C_0_SDA/GPIO_22		
J14	I2C_1_SCL/GPIO_31	I2C_1_SCL/GPIO_31	I2C_1_SCL/GPIO_31		
J15	VCCMSSIOB2	VCCMSSIOB2	VCCMSSIOB2		
J16	I2C_1_SDA/GPIO_30	I2C_1_SDA/GPIO_30	I2C_1_SDA/GPIO_30		
K1	GPIO_1/IO32RSB4V0	MAC_MDIO/IO49RSB4V0	MAC_MDIO/IO58RSB4V0		
K2	GPIO_0/IO33RSB4V0	MAC_MDC/IO48RSB4V0	MAC_MDC/IO57RSB4V0		
K3	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4		
K4	MSS_RESET_N	MSS_RESET_N	MSS_RESET_N		
K5	VCCRCOSC	VCCRCOSC	VCCRCOSC		
K6	VCCMSSIOB4	VCCMSSIOB4	VCCMSSIOB4		
K7	GND	GND	GND		
K8	VCC	VCC	VCC		
K9	GND	GND	GND		
K10	VCC	VCC	VCC		
K11	GND	GND	GND		
Notes:		•	•		

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.

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SmartFusion Customizable System-on-Chip (cSoC)

	FG	484
Pin Number	A2F200 Function	A2F500 Function
L9	VCC	VCC
L10	GND	GND
L11	VCC	VCC
L12	GND	GND
L13	VCC	VCC
L14	GND	GND
L15	VCC	VCC
L16	GND	GND
L17	GNDQ	GNDQ
L18	GDA2/IO33NDB1V0	GDA2/IO42NDB1V0
L19	VCCFPGAIOB1	VCCFPGAIOB1
L20	GDB1/IO30PDB1V0	GDB1/IO39PDB1V0
L21	GDB0/IO30NDB1V0	GDB0/IO39NDB1V0
L22	GDC2/IO32PDB1V0	GDC2/IO41PDB1V0
M1	NC	IO71PDB5V0
M2	NC	IO71NDB5V0
M3	VCCFPGAIOB5	VCCFPGAIOB5
M4	NC	IO72NPB5V0
M5	GNDQ	GNDQ
M6	NC	IO68PDB5V0
M7	GND	GND
M8	VCC	VCC
M9	GND	GND
M10	VCC	VCC
M11	GND	GND
M12	VCC	VCC
M13	GND	GND
M14	VCC	VCC
M15	GND	GND
M16	VCCFPGAIOB1	VCCFPGAIOB1
M17	NC	NC
M18	GDB2/IO33PDB1V0	GDB2/IO42PDB1V0
M19	VJTAG	VJTAG
M20	GND	GND

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.



	FG	484
Pin Number	A2F200 Function	A2F500 Function
M21	VPP	VPP
M22	IO32NDB1V0	IO41NDB1V0
N1	GND	GND
N2	NC	IO70PDB5V0
N3	NC	IO70NDB5V0
N4	VCCRCOSC	VCCRCOSC
N5	VCCFPGAIOB5	VCCFPGAIOB5
N6	NC	IO68NDB5V0
N7	VCCFPGAIOB5	VCCFPGAIOB5
N8	GND	GND
N9	VCC	VCC
N10	GND	GND
N11	VCC	VCC
N12	GND	GND
N13	VCC	VCC
N14	GND	GND
N15	VCC	VCC
N16	NC	GND
N17	NC	NC
N18	VCCFPGAIOB1	VCCFPGAIOB1
N19	VCCENVM	VCCENVM
N20	GNDENVM	GNDENVM
N21	NC	NC
N22	GND	GND
P1	NC	IO69NDB5V0
P2	NC	IO69PDB5V0
P3	GNDRCOSC	GNDRCOSC
P4	GND	GND
P5	NC	NC
P6	NC	NC
P7	GND	GND
P8	VCC	VCC
P9	GND	GND
P10	VCC	VCC

Notes:

1. Shading denotes pins that do not have completely identical functions from density to density. For example, the bank assignment can be different for an I/O, or the function might be available only on a larger density device.



Datasheet Information

Revision	Changes	Page
	The A2F060 device was added to product information tables.	N/A
	The "Product Ordering Codes" table was updated to removed Std. speed and add speed grade 1. Pre-production was removed from the application ordering code category.	VI
	The "SmartFusion cSoC Block Diagram" was revised.	IV
	The "Datasheet Categories" section was updated, referencing the "SmartFusion cSoC Block Diagram" table, which is new.	1-4, IV
	The "VCCI" parameter was renamed to "VCCxxxxIOBx." "Advanced I/Os" were renamed to "FPGA I/Os."	N/A
	Generic pin names that represent multiple pins were standardized with a lower case x as a placeholder. For example, VAREFx designates VAREF0, VAREF1, and VAREF2. Modes were renamed as follows:	
	Operating mode was renamed to SoC mode.	
	32KHz Active mode was renamed to Standby mode.	
	Battery mode was renamed to Time Keeping mode.	
	Table entries have been filled with values as data has become available.	
	Table 2-1 • Absolute Maximum Ratings, Table 2-2 • Analog Maximum Ratings, and Table 2-3 • Recommended Operating Conditions <sup>5,6</sup> were revised extensively.	2-1 through 2-3
	Device names were updated in Table 2-6 • Package Thermal Resistance.	2-7
	Table 2-8 • Power Supplies Configuration was revised extensively.	2-10
	Table 2-11 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings was revised extensively.	2-11
	Removed "Example of Power Calculation."	N/A
	Table 2-14 • Different Components Contributing to Dynamic Power Consumption in SmartFusion cSoCs was revised extensively.	2-12
	Table 2-15 • Different Components Contributing to the Static Power Consumption in SmartFusion cSoCs was revised extensively.	2-13
	The "Power Calculation Methodology" section was revised.	2-14
	Table 2-83 • Electrical Characteristics of the RC Oscillator was revised extensively.	2-61
	Table 2-85 • Electrical Characteristics of the Low Power Oscillator was revised extensively.	2-62
	The parameter t <sub>RSTBQ</sub> was changed to T <sub>C2CWRH</sub> in Table 2-87 • RAM4K9.	2-69
	The 12-bit mode row for integral non-linearity was removed from Table 2-95 • ADC Specifications. The typical value for 10-bit mode was revised. The table note was punctuated correctly to make it clear.	2-81
	Figure 37-34 • Write Access after Write onto Same Address, Figure 37-34 • Read Access after Write onto Same Address, and Figure 37-34 • Write Access after Read onto Same Address were deleted.	N/A
	Table 2-99 • Voltage Regulator was revised extensively.	2-87
	The "Serial Peripheral Interface (SPI) Characteristics" section and "Inter-Integrated Circuit ( $I^2C$ ) Characteristics" section are new.	2-89, 2-91